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BUK7Y9R9-80E

N-channel 80 V, 9.9 mΩ standard level MOSFET in LPAK56

8 May 2013

Product data sheet

1. General description

Standard level N-channel MOSFET in an LPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with $V_{GS(th)}$ rating of greater than 1 V at 175 °C

3. Applications

- 12 V, 24 V and 48 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	80	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C}; \text{Fig. 1}$	-	-	89	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}; \text{Fig. 2}$	-	-	195	W
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ °C}; \text{Fig. 11}$	-	7.3	9.9	mΩ
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; V_{DS} = 64\text{ V}; \text{Fig. 13}; \text{Fig. 14}$	-	14.4	-	nC



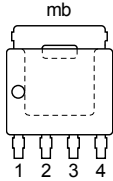
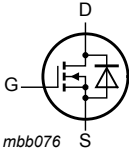
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N-channel 80 V, 9.9 mΩ standard level MOSFET in LPAK56

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>LPAK56; Power-SO8 (SOT669)</p>	
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7Y9R9-80E	LPAK56; Power-SO8	Plastic single-ended surface-mounted package (LPAK56; Power-SO8); 4 leads	SOT669

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7Y9R9-80E	79E980

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$	-	80	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	80	V
V_{GS}	gate-source voltage	$T_j \leq 175\text{ °C}$; DC	-20	20	V
I_D	drain current	$T_{mb} = 25\text{ °C}$; $V_{GS} = 10\text{ V}$; Fig. 1	-	89	A
		$T_{mb} = 100\text{ °C}$; $V_{GS} = 10\text{ V}$; Fig. 1	-	63	A
I_{DM}	peak drain current	$T_{mb} = 25\text{ °C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$; Fig. 4	-	354	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Fig. 2	-	195	W
T_{stg}	storage temperature		-55	175	°C

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BUK7Y9R9-80E

N-channel 80 V, 9.9 mΩ standard level MOSFET in LPAK56

Symbol	Parameter	Conditions	Min	Max	Unit
T_j	junction temperature		-55	175	°C
Source-drain diode					
I_S	source current	$T_{mb} = 25\text{ °C}$	-	89	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\ \mu\text{s}$; $T_{mb} = 25\text{ °C}$	-	354	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 89\text{ A}$; $V_{sup} \leq 80\text{ V}$; $R_{GS} = 50\ \Omega$; $V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ °C}$; unclamped; Fig. 3	[1][2]	106	mJ

[1] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[2] Refer to application note AN10273 for further information.

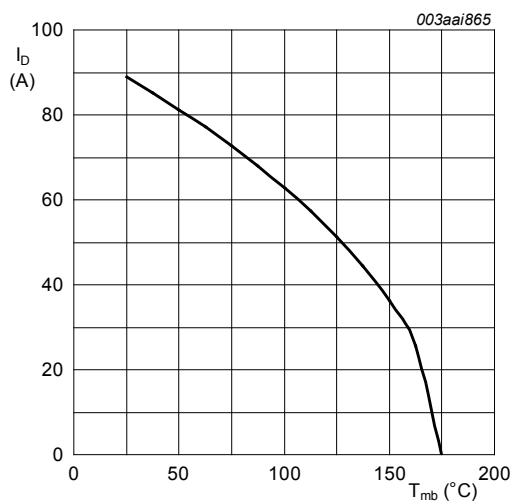


Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \geq 10V$$

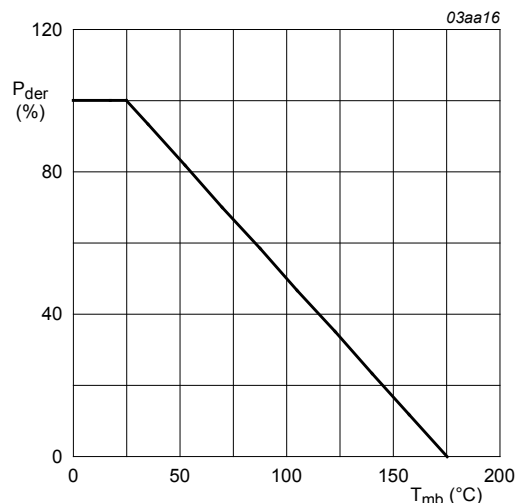


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100\%$$

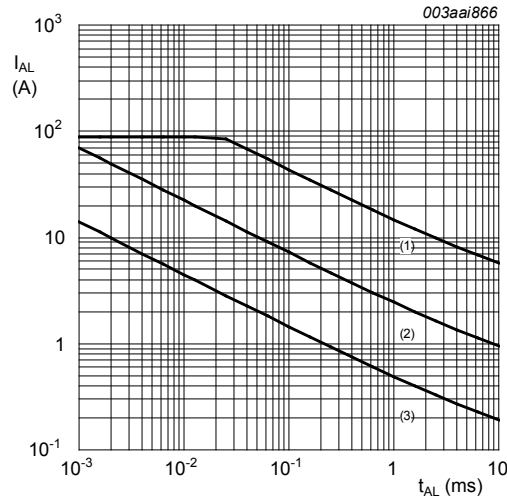


Fig. 3. Avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j (init)} = 25^{\circ}C$; (2) $T_{j (init)} = 150^{\circ}C$; (3) Repetitive Avalanche

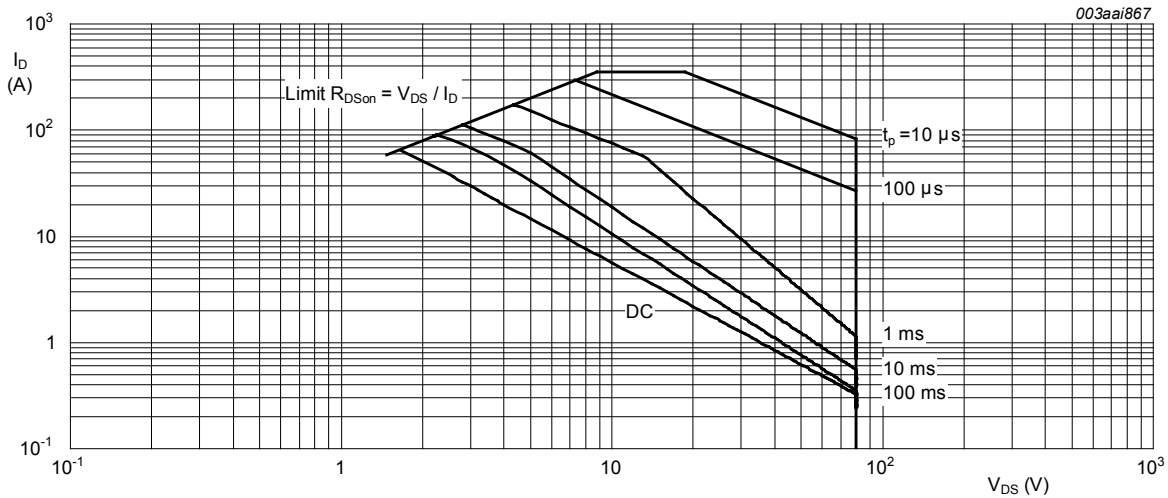


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^{\circ}C$; I_{DM} is a single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	-	0.77	K/W

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N-channel 80 V, 9.9 mΩ standard level MOSFET in LPAK56

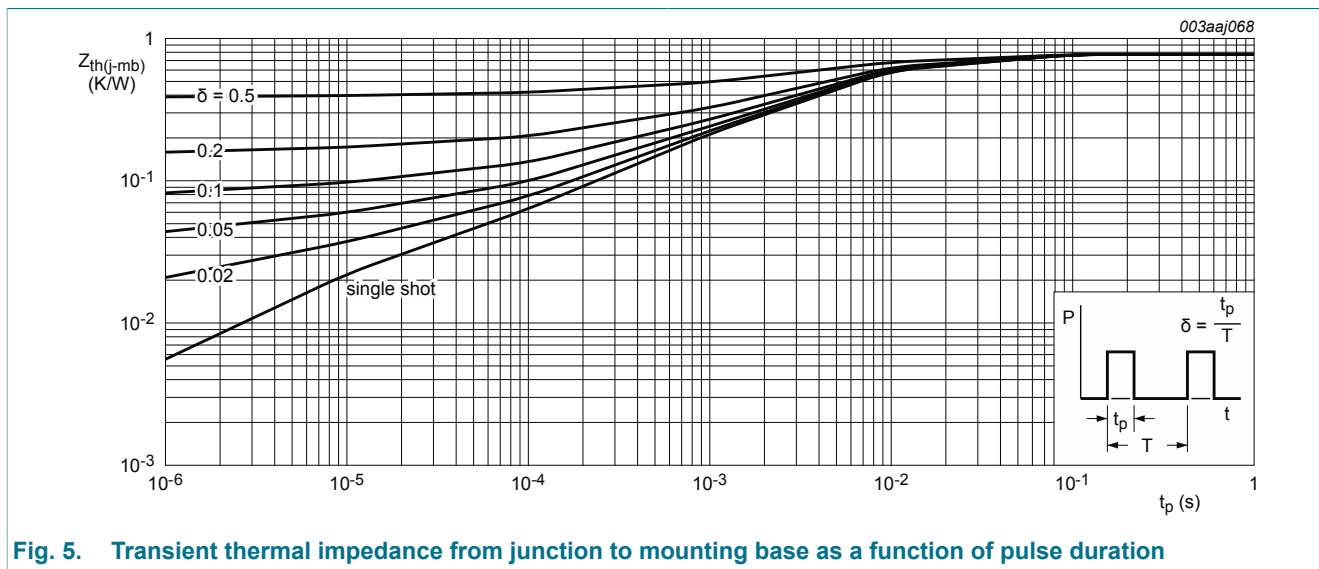


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

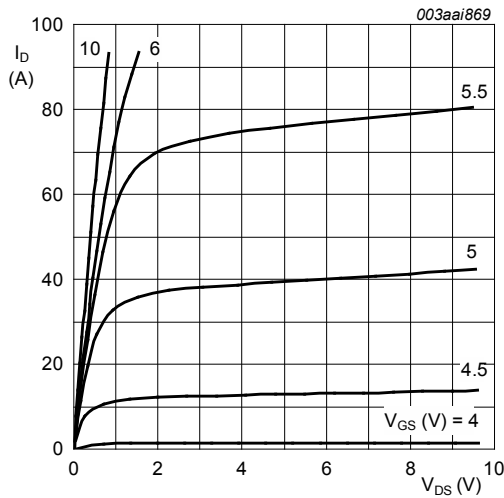
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _J = 25 °C	80	-	-	V
		I _D = 250 μA; V _{GS} = 0 V; T _J = -55 °C	72	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _J = 25 °C; Fig. 9 ; Fig. 10	2.4	3	4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _J = -55 °C; Fig. 9	-	-	4.5	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _J = 175 °C; Fig. 9	1	-	-	V
I _{DSS}	drain leakage current	V _{DS} = 80 V; V _{GS} = 0 V; T _J = 25 °C	-	0.13	10	μA
		V _{DS} = 80 V; V _{GS} = 0 V; T _J = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _J = 25 °C	-	2	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _J = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _J = 175 °C; Fig. 11 ; Fig. 12	-	-	24.9	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _J = 25 °C; Fig. 11	-	7.3	9.9	mΩ
Dynamic characteristics						
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 64 V; V _{GS} = 10 V; Fig. 13 ; Fig. 14	-	51.6	-	nC
Q _{GS}	gate-source charge		-	14.1	-	nC
Q _{GD}	gate-drain charge		-	14.4	-	nC

NXP Semiconductors

BUK7Y9R9-80E

N-channel 80 V, 9.9 mΩ standard level MOSFET in LPAK56

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
C_{iss}	input capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}; f = 1\text{ MHz}; T_j = 25\text{ }^\circ\text{C}; \text{Fig. 15}$	-	3200	4266	pF
C_{oss}	output capacitance		-	303	364	pF
C_{rss}	reverse transfer capacitance		-	165	226	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 60\text{ V}; R_L = 2.4\text{ }\Omega; V_{GS} = 10\text{ V}; R_{G(ext)} = 5\text{ }\Omega$	-	15	-	ns
t_r	rise time		-	23	-	ns
$t_{d(off)}$	turn-off delay time		-	34	-	ns
t_f	fall time		-	21	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 25\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}; \text{Fig. 16}$	-	0.83	1.2	V
t_{rr}	reverse recovery time	$I_S = 20\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}$	-	35	-	ns
Q_r	recovered charge		-	52	-	nC



$T_j = 25\text{ }^\circ\text{C}; t_p = 300\text{ }\mu\text{s}$

Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

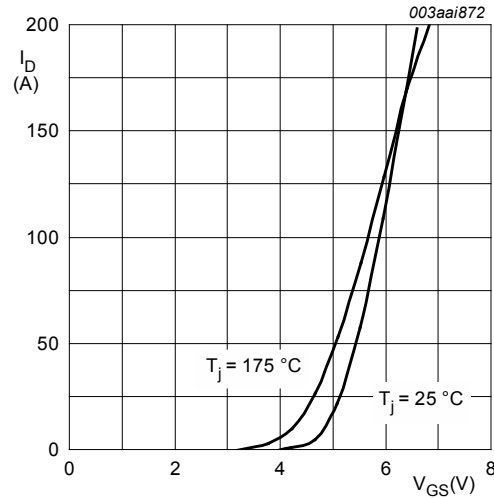


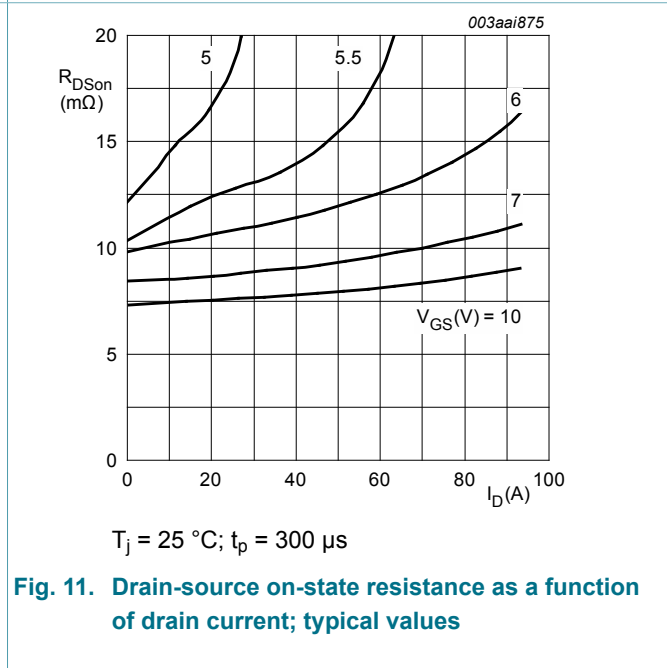
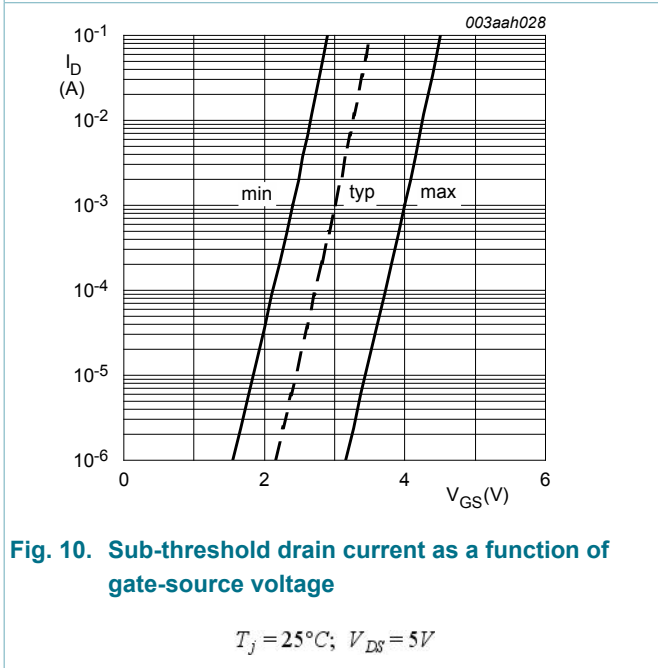
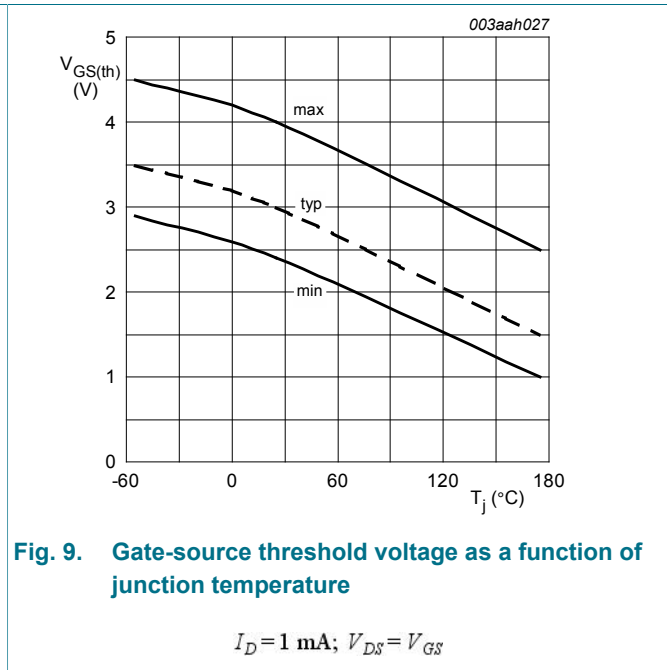
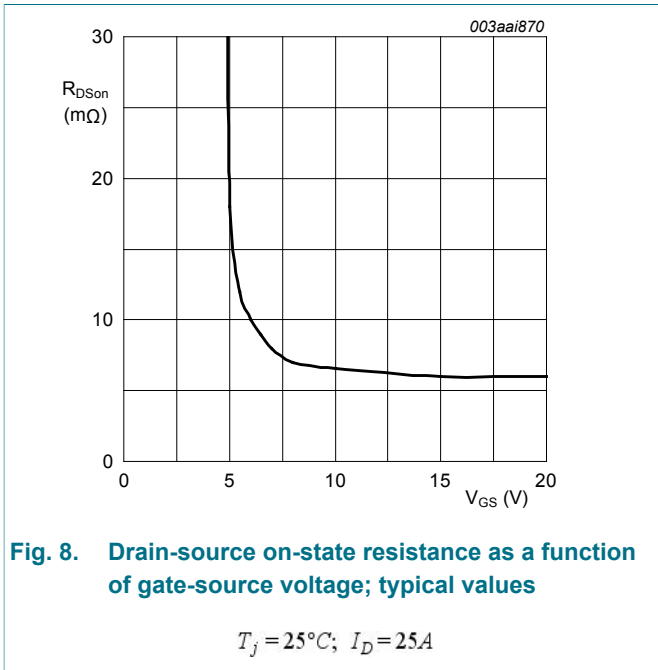
Fig. 7. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$V_{DS} = 10\text{ V}$

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N-channel 80 V, 9.9 mΩ standard level MOSFET in LFPK56



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N-channel 80 V, 9.9 mΩ standard level MOSFET in LPAK56

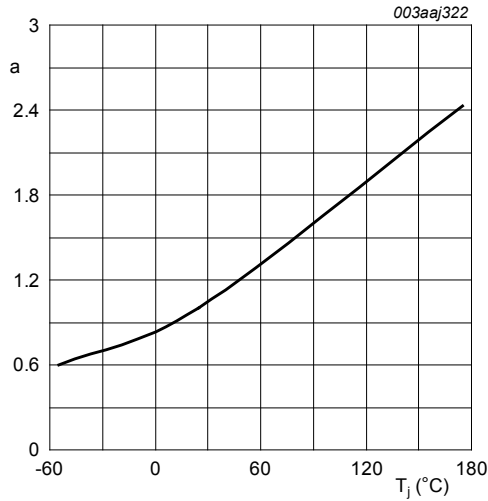


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DS(on)}}{R_{DS(on)}(25^\circ C)}$$

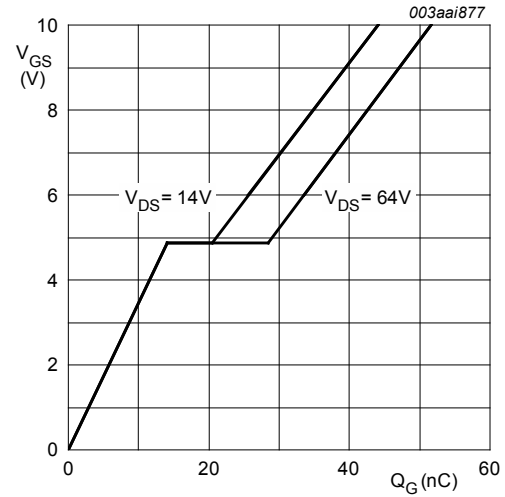


Fig. 13. Gate-source voltage as a function of gate charge; typical values

$T_j = 25^\circ C; I_D = 25A$

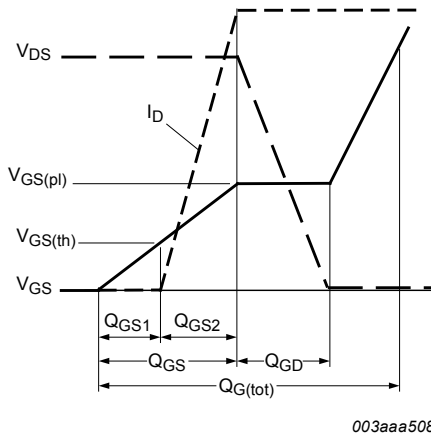


Fig. 14. Gate charge waveform definitions

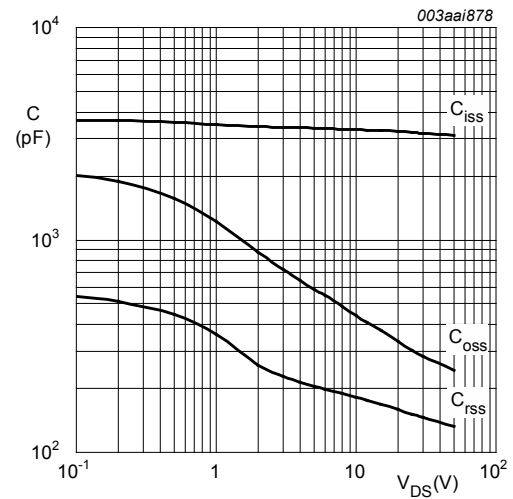


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0V; f = 1MHz$

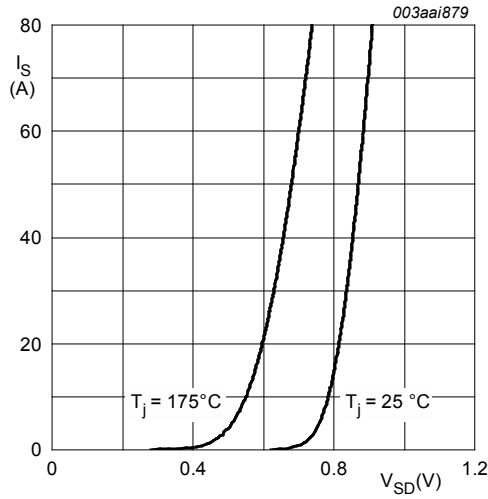


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

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N-channel 80 V, 9.9 mΩ standard level MOSFET in LPAK56

11. Package outline

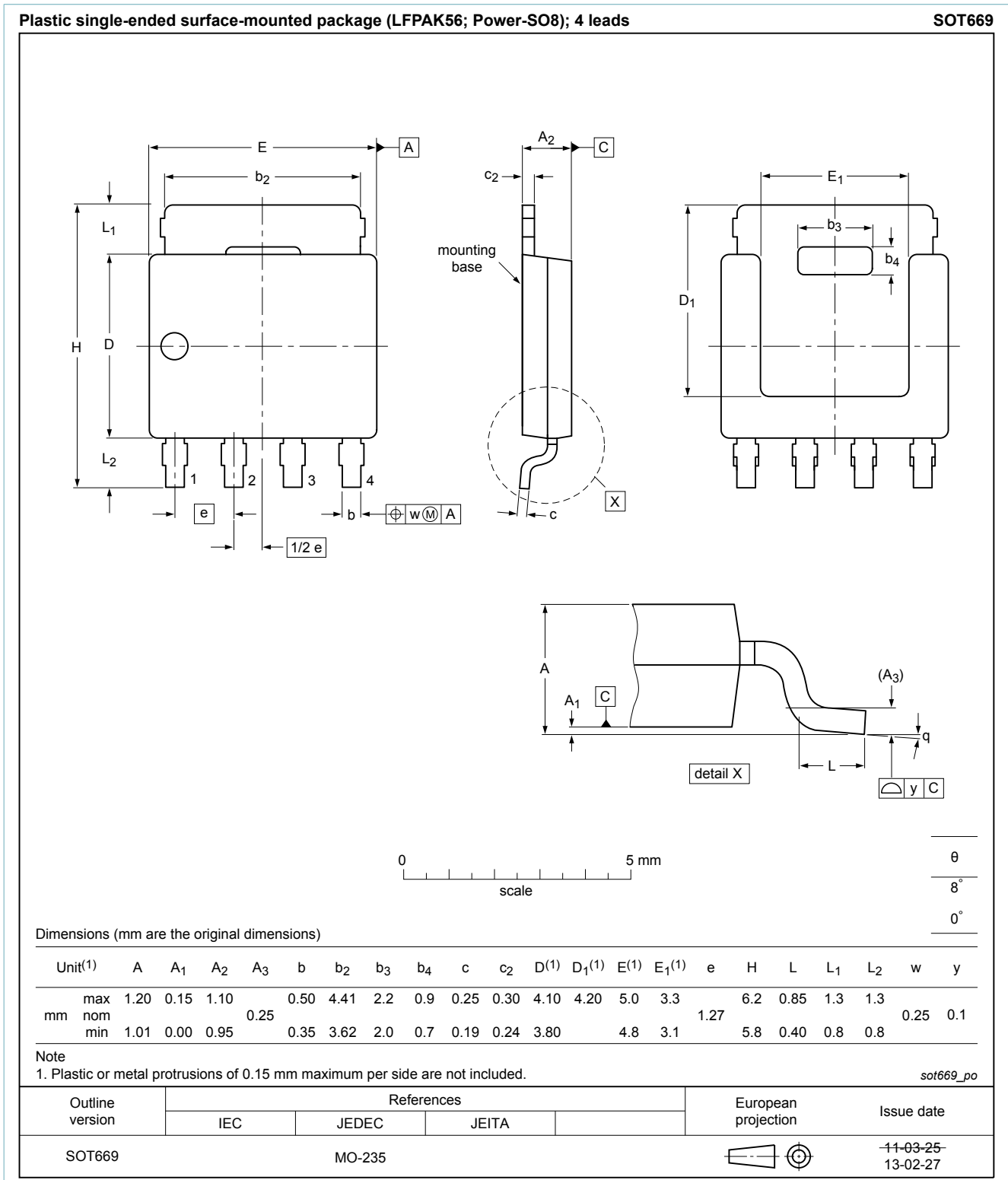


Fig. 17. Package outline LPAK56; Power-SO8 (SOT669)

12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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13. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	2
9	Thermal characteristics	4
10	Characteristics	5
11	Package outline	10
12	Legal information	11
12.1	Data sheet status	11
12.2	Definitions	11
12.3	Disclaimers	11
12.4	Trademarks	12

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